

Amendments to the claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method for manufacturing a metal master comprising the steps of:

forming a conductive film by an electroless plating method on a glass master having fine depressions and protrusions for forming an information recording region of an information recording disc;

forming an electrolytic plating layer by an electrolytic plating method on the conductive film; and

removing the conductive film and the electrolytic plating layer from the glass master to provide a metal master, wherein master:

wherein the conductive film is formed to have a thickness of 35 to 200 nm.

2. (Currently Amended) The method for manufacturing a metal master according to claim 1, wherein

the conductive film is formed to have a thickness of 40 nm or more.

3. (Currently Amended) The method for manufacturing a metal master according to claim 1, wherein

the conductive film is formed to have a thickness of 45 nm or more.

4. (Currently Amended) The method for manufacturing a metal master according to claim 1, wherein

the conductive film is formed to have a thickness of 50 nm or more.

5. (Currently Amended) The method for manufacturing a metal master according to claim 1, wherein

the conductive film is formed to have a thickness of 150 nm or less.

6. (Currently Amended) The method for manufacturing a metal master according to claim 1, wherein

the conductive film is formed to have a thickness of 120 nm or less.

7. (Currently Amended) The method for manufacturing a metal master according to claim 1, wherein

the conductive film is formed to have a thickness of 90 nm or less.

8. (Currently Amended) The method for manufacturing a metal master according to claim 1, wherein

the conductive film is formed to have a thickness of 60 nm or less.

9. (Currently Amended) The method for manufacturing a metal master according to claim 1, wherein

the conductive film is formed to have a thickness of 55 nm or less.

10. (Currently Amended) A method for manufacturing a metal master comprising the steps of:

forming a conductive film by an electroless plating method on a glass master having fine depressions and protrusions for forming an information recording region of an information recording disc;

forming an electrolytic plating layer by an electrolytic plating method on the conductive film; and

removing the conductive film and the electrolytic plating layer from the glass master to provide a metal master, wherein master;

wherein the conductive film is formed to have a thickness greater than a step height of the fine depressions and protrusions of the glass master.

11. (Currently Amended) A metal master comprising a conductive film having copied fine depressions and protrusions for forming an information recording region of an information recording disc, and an electrolytic plating layer formed on the conductive film, wherein

the conductive film has a thickness in the range of 35 to 200 nm and is greater than a step height of the fine depressions and protrusions.

12. (Currently Amended) The metal master according to claim 11, wherein

the thickness of the conductive film is 40 nm or more.

13. (Currently Amended) The metal master according to claim 11, wherein

the thickness of the conductive film is 45 nm or more.

14. (Currently Amended) The metal master according to claim 11, wherein

the thickness of the conductive film is 50 nm or more.

15. (Currently Amended) The metal master according to claim 11, wherein

the thickness of the conductive film is 150 nm or less.

16. (Currently Amended) The metal master according to claim 11, wherein

the thickness of the conductive film is 120 nm or less.

17. (Currently Amended) The metal master according to claim 11, wherein

the thickness of the conductive film is 90 nm or less.

18. The metal master according to claim 11, wherein

_____the thickness of the conductive film is 60 nm or less.

19. (Currently Amended) The metal master according to claim 11, wherein
_____the thickness of the conductive film is 55 nm or less.